

N-Channel MOSFETs (>500V...900V); Package: PG-TO263-3; VDS (max): 600.0 V; Package: D2PAK (TO-263); RDS(ON) @ TJ=25°C VGS=10: 199.0 mOhm; ID(max) @ TC=25°C: 16.0 A; IDpuls (max): 51.0 A; MOSFET COOL MOS PWR TRANS MAX 650V

Manufacturers	<u>Infinion Technologies Corporation</u>
Package/Case	TO-263
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPB60R199CP or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPB60R199CP is a power MOSFET transistor manufactured by Infineon Technologies.

Features

- It has a drain-source voltage rating of 650V
- It has a maximum continuous drain current rating of 60A
- It has a low on-resistance of 0.033 ohms
- It has a fast switching capability
- It is designed with a high di/dt capability, which makes it suitable for use in high-frequency switching applications

Application

- AC-DC power supplies
- DC-DC converters
- Motor control
- Lighting applications
- Solar inverters
- Uninterruptible power supplies (UPS)



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



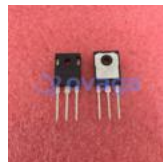
[IPB180N06S4-H1](#)

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PG-TO263-7-3



[IPG20N04S4-12](#)

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[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

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